

Tunable Periodic Nanopillar Array for MAPbI₃ Perovskite Photodetectors with Improved Light Absorption

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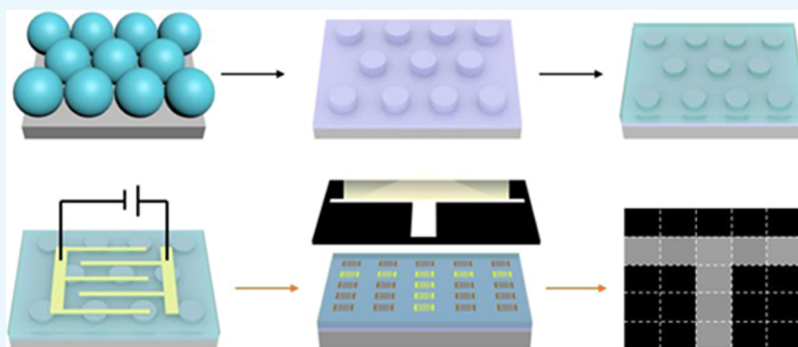
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ABSTRACT: In the field of optoelectronic applications, the vigorous development of organic–inorganic hybrid perovskite materials, such as methylammonium lead triiodide (MAPbI₃), has spurred continuous research on methods to enhance the photodetection performance. Periodic nanoarrays can effectively improve the light absorption of perovskite thin films. However, there are still challenges in fabricating tunable periodic and large-area perovskite nanoarrays. In this study, we present a cost-effective and facile approach utilizing nanosphere lithography and dry etching techniques to create a large-area Si nanopillar array, which is employed for patterning MAPbI₃ thin films. The scanning electron microscopy (SEM) and X-ray diffraction (XRD) results reveal that the introduction of nanopillar structures did not have a significant adverse effect on the crystallinity of the MAPbI₃ thin film. Light absorption tests and optical simulations indicate that the nanopillar array enhances the light intensity within the perovskite films, leading to photodetectors with a responsivity of 11.2 A/W and a detectivity of 7.3×10^{10} Jones at 450 nm in wavelength. Compared with photodetectors without nanostructures, these photodetectors exhibit better visible light absorption. Finally, we demonstrate the application of these photodetector arrays in a prototype image sensor.

1. INTRODUCTION

Photodetectors that convert incident light (ultraviolet, visible, or infrared) into electrical signals are pivotal in numerous industrial and scientific fields, including optical communication, environmental monitoring, day and night monitoring, and chemical and biological sensing.^{1–3} For high-performance photodetection, materials with low cost, high optical absorption coefficient, narrow direct band gap, and fast response rate are imperative.^{4–6} Many materials have been explored for photon detection, including graphene,^{7–9} colloidal nanocrystals,^{10–12} metal oxides,^{13–15} and metal halide perovskites and their hybrids.^{16–18} In particular, organic–inorganic hybrid perovskites, such as methylammonium lead trihalide (MAPbX₃, where MA = CH₃NH₃, X = Cl, Br, or I), have gained increasing attention due to their high optical absorption coefficient, carrier mobility, and long diffusion length over a wide spectral range.^{19–21} Thus, they are considered a promising candidate for next-generation photodetection applications. In recent years, people have been continuously striving to optimize surface defects, control crystal growth, and

improve light-trapping ability of organic–inorganic hybrid perovskite films to optimize the performance of photodetectors.^{22–24}

Although metal halide perovskite exhibits excellent performance for high-performance photodetectors, their susceptibility to moisture and oxygen in the air can curtail their potential applications,²⁵ and the grain boundary effect and internal decomposition have a significant impact on the performance of perovskite devices. These defects are prone to appear at the interface and grain boundaries of perovskite films, which reduce the probability of radiation recombination and lead to trap states related to grain boundaries.^{26,27} Therefore, it is critical to slow down the decomposition process and improve

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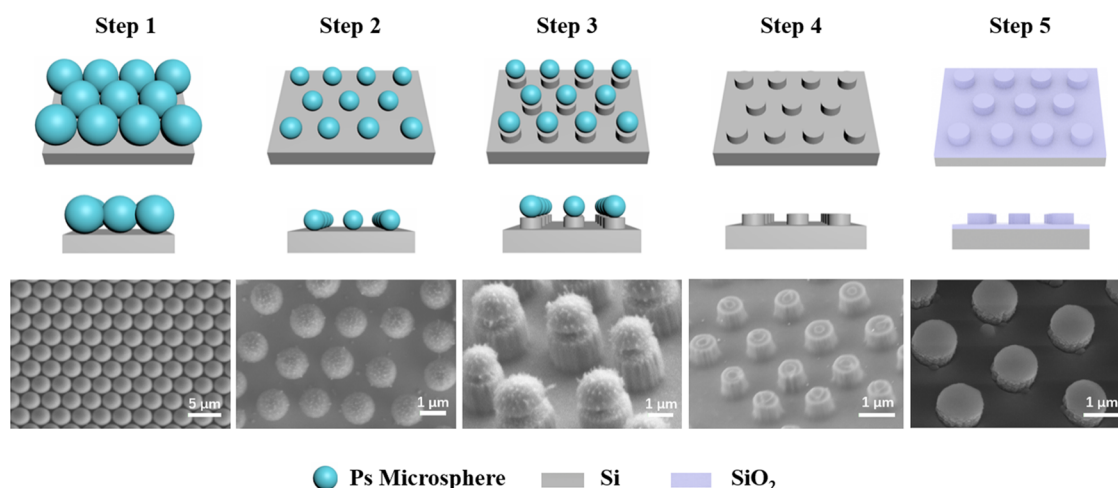


Figure 1. Schematic diagram of the produced nanopillar array by microsphere lithography, dry etching, and related scanning electron microscopy images. Step 1: spread a single layer of polyethylene (PS) spheres onto a Si substrate (top view SEM). Step 2: reduced the diameter of the PS spheres via O_2 plasma etching (top view SEM). Step 3: fabricated nanopillars' structures via dry etching (45° top view SEM). Step 4: removed the PS spheres on the nanopillars via oxygen plasma (45° top view SEM). Step 5: evaporated a 200 nm-thick SiO_2 layer onto Si nanopillars (45° top view SEM).

the stability and performance of the device.^{28,29} For instance, Jeong et al. used pseudo-halide anionic formate ($HCOO^-$) to suppress anionic vacancy defects present at grain boundaries and perovskite film surfaces, improving the film's crystallinity.³⁰ Wu et al.³¹ incorporated 1-butyl-3-methylimidazolium tetrafluoroborate (BMIMBF₄) as an additive into methylammonium lead triiodide (MAPbI₃) nanowires, effectively passivating defects, inhibiting the degradation of perovskite, and leading to the formation of nanochannels, achieving rapid charge transfer. Other methods such as introducing a polymer modification³² and using a two-step imprinting technique³³ have been shown to enhance the stability of films.

The light absorption ability of the films greatly affects the performance of photodetectors. By properly designing periodic light capture nanostructures, light scattering can be increased, resulting in enhanced light absorption ability, which can improve the performance of the photodetectors.^{34,35} Although periodic nanoarray structures exhibit good repeatability and tunability compared with nonordered nanostructures, manufacturing large-area periodic arrays such as nanowires and nanotubes generally requires complex and expensive commercial lithography techniques such as electron beam lithography or focused ion beam lithography. Therefore, to achieve high-performance nanostructured organic–inorganic hybrid perovskite photodetectors on an affordable scale, it is necessary to explore and develop economical nanomanufacturing methods.

In recent years, various methods such as orthogonal lithography,^{36,37} nanosphere lithography,^{38–40} chemical stripping lithography,⁴¹ self-collapse lithography,⁴² nanoimprint methods,^{43–45} and photolithography⁴⁶ have been developed to prepare large-area submicrometer patterns. These strategies have low cost and high repeatability and have been widely used to fabricate nanostructured devices.^{47–49} For instance, Wang et al. realized a high-performance patterned perovskite photodetector at the nanometer level through nanoimprint lithography; the crystallinity and optical properties of the perovskite have been improved, which contribute to higher mobility, longer diffusion length, and better photon absorption.⁵⁰ By rationally designing light-trapping nanostructures,

the crystallinity and light absorption of perovskite films can be increased, leading to improved device performance.⁵¹

In this work, utilizing nanosphere lithography and dry etching, we prepared a large-area-ordered nanopillar array structure for fabricating organic–inorganic hybrid perovskite films. The diameters, heights, and pitch of the nanopillars can be precisely controlled. Through spin coating, we deposited the MAPbI₃ thin film to fill and cover the entire periodic nanopillar array, thus enhancing the light absorption and photoelectric sensitivity of the photodetectors. Additionally, we further studied the effect of the periodic nanopillar array through a COMSOL multiphysics simulation. To demonstrate our method, we fabricated an image sensor composed of a 5×5 photodetector array that exhibited good imaging functionality. This strategy not only improves the photoelectric performance of the device with good repeatability but also provides a basis for the development of large-area nanostructured organic–inorganic hybrid perovskite thin-film photodetectors.

2. MATERIALS AND METHODS

2.1. Materials. Polystyrene (PS) spheres with sizes from 500 nm to 2 μ m were purchased from Rigor Bioscience Development Inc. Methylammonium lead iodide ($CH_3NH_3PbI_3$) was purchased from Xi'an Polymer Light Technology Corp. All of the materials and reagents were used as received.

2.2. Fabrication of Nanopillar Arrays. Si substrates were cleaned with isopropyl alcohol, acetone, and deionized water for 10 min and dried using a nitrogen gas gun. Then, the cleaned Si substrates were treated using an oxygen plasma cleaner at 150 W for 600 s. Then, the substrates were covered with a tightly packed monolayer of PS spheres. The diameters of the PS spheres were reduced by oxygen plasma at 200 W. Dry etching was performed in a gas atmosphere of C_4F_8 and SF_6 for 2 min to obtain nanopillars. The PS spheres were eliminated on the nanopillar through 5 min of oxygen plasma. Finally, silicon dioxide with a thickness of 200 nm was deposited on the surface of the Si substrate with the nanopillar array by thermal evaporation.

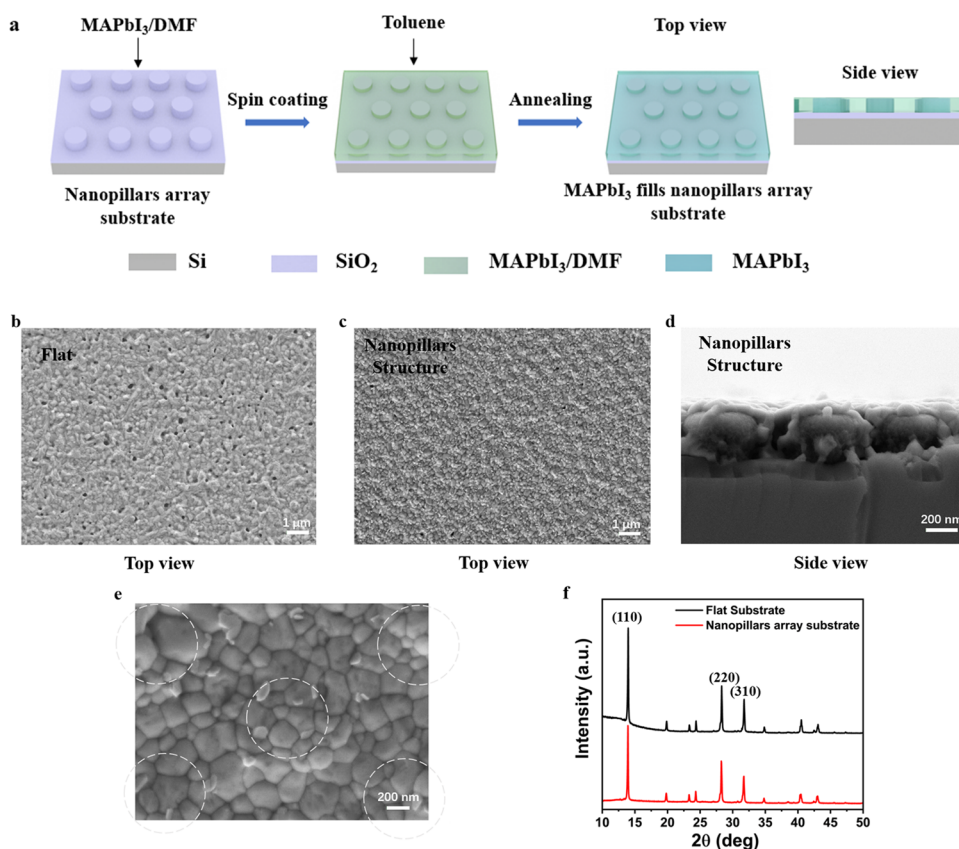


Figure 2. (a) Schematic coating process of the MAPbI₃ film on nanopillar arrays of SiO₂/Si. (b) Typical SEM images of the MAPbI₃ film fabricated on the flat substrate (top view). (c, e) Typical SEM images of the MAPbI₃ film fabricated on the nanopillar substrate (top view). (d) Cross-sectional SEM image of the MAPbI₃ film on the nanopillar substrate (side view). (f) XRD patterns of the MAPbI₃ film based on the nanopillar array substrate and flat substrate.

2.3. Fabrication of MAPbI₃ Thin Film on Nanopillar Substrates. 50 μ L portion of 1 M MAPbI₃ perovskite precursor solution in *N,N*-dimethylformamide was spin-coated on the nanopillar substrate at 3000 rpm for 45 s. During spin coating, 100 μ L of toluene was added dropwise on the substrate. Then, the sample was annealed at 100 $^{\circ}$ C for 10 min to form MAPbI₃ on the nanopillar substrate.

2.4. Fabrication of Perovskite Photodetectors. The electrodes of the photodetectors were fabricated by thermal evaporation of copper under a shadow mask, which had a thickness of 200 nm. Photodetectors based on S-1, S-2, S-3, and flat samples were fabricated under identical conditions.

3. RESULTS AND DISCUSSION

3.1. Preparation of SiO₂/Si Nanopillar Substrates. We combine nanosphere lithography and dry etching techniques to fabricate a large-area periodically tunable nanopillar array on silicon wafers and then evaporate a SiO₂ layer onto Si nanopillars, which serves as a substrate for MAPbI₃ thin films, as illustrated in Figure 1.

3.1.1. Step 1. Spread a single layer of polyethylene (PS) spheres with diameters of 2 μ m, 1 μ m, and 500 nm onto a Si (100) substrate to form a dense stack and submicrometer features.

3.1.2. Step 2. The diameters of the PS spheres were reduced by half via oxygen plasma for 30 (for 500 nm diameter PS nanospheres), 75 (for 1 μ m diameter PS microspheres), and 180 s (for 2 μ m diameter PS microspheres) (Figure 1 as well as Figures S1 and S2 in the Supporting Information).

3.1.3. Step 3. Low aspect ratio Si nanostructures with smooth sidewalls were directly obtained via dry etching, which simultaneously used C₄F₈ and SF₆ as etching and passivation gases for 2 min.

3.1.4. Step 4. The PS spheres on the nanopillars were removed via oxygen plasma for 5 min, exposing a large area of periodic nanopillars with diameters of 1 μ m, 500 nm, and 250 nm and a height of 400 \pm 30 nm (Figures S3 in the Supporting Information).

3.1.5. Step 5. A 200 nm-thick SiO₂ layer was evaporated onto the Si nanopillars by thermal vapor deposition. Then, a large area of the SiO₂/Si nanopillar array with diameters of 1 μ m, 500 nm, and 250 nm was fabricated (Figure S4 in the Supporting Information).

3.2. Preparation of MAPbI₃ Thin Films. When the preparation of the nanostructured substrates was complete, MAPbI₃ was spin-coated on the SiO₂/Si substrate with nanopillars and the flat SiO₂/Si substrate, respectively. During spin coating, toluene was added dropwise as an antisolvent to promote the crystallization of MAPbI₃, followed by a thermal annealing process to increase crystallinity (Figure 2a). (More details are in the Supporting Information.)

As shown in Figure 2b, the MAPbI₃ thin film on the flat substrate does not have a specific submicrometer structure, and there are some pores on the surface (Figure S5). On the contrary, due to the periodic distribution of the nanopillar array, Figure 2c shows that the thin film with nanopillars exhibited a large-area patterned periodic morphology (Figure S5). The MAPbI₃ thin film completely covered the entire

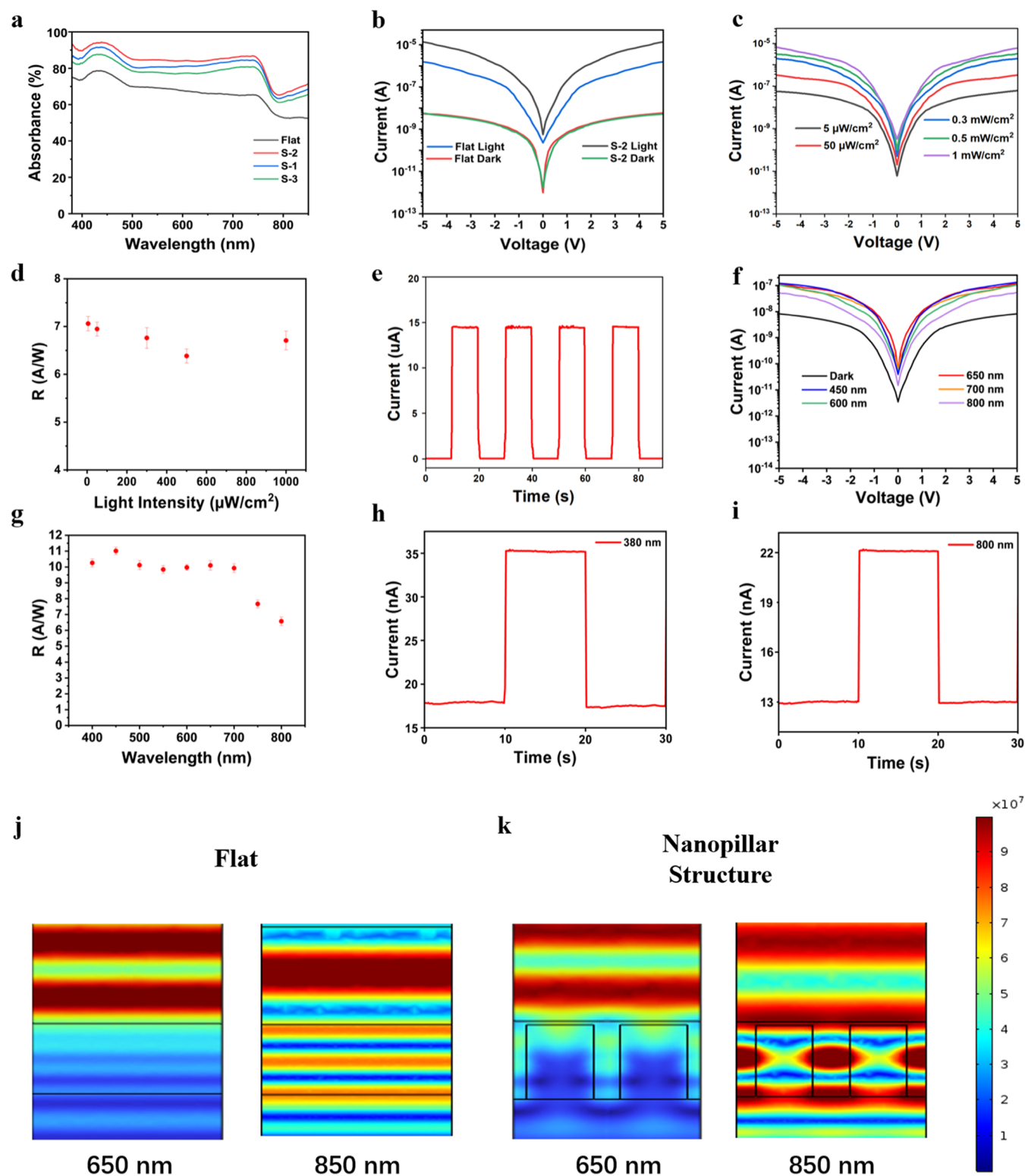


Figure 3. (a) Measured absorption spectra of MAPbI₃ films on SiO₂/Si nanopillar substrates and flat substrates from 380 to 850 nm. (b) Dark/photocurrent of the photodetectors based on flat substrates and nanopillar substrates. The incident white light intensity is 2.5 mW/cm². (c) *I*–*V* curves of the photodetectors (sample S-2) measured in the dark and under white light illumination with a range of light intensity. (d) Plots of responsivity of the photodetector (sample S-2) as a function of light intensity under white light. (e) Time-resolved photoresponse of the photodetector; the incident light intensity is 2.5 mW/cm². (f) *I*–*V* curves of the S-2 at different wavelengths; the incident light intensity is 10 μW/cm². (g) Plots of responsivity of the photodetector (sample S-2) as a function of light intensity at different wavelengths; the incident light intensity is 10 μW/cm². (h, i) Time-resolved photoresponse of the photodetector at 380 and 800 nm, respectively. The incident light intensity is 10 μW/cm². (j, k) Magnitude of the electric field obtained from COMSOL simulations for MAPbI₃ films on flat substrates and SiO₂/Si nanopillar substrates under light illumination at 650 and 850 nm.

nanopillar array, with a thickness of 450 nm (Figure 2d), which is relatively dense, with uniform grain distribution (Figure 2e); a histogram of the particle size distribution is shown in Figure S6. Through SEM images and particle size distribution histograms, we can find that the particle sizes of the MAPbI₃ thin film based on different substrates are relatively similar without significant differences. X-ray diffraction patterns (XRD) of the MAPbI₃ thin films on different substrates are shown in Figure 2f. The diffraction pattern shows peaks among the following angles: 14.1, 28.5, 31.9, 40.5, and 43.2°, which correspond to the (110), (220), (310), (224), and (314) planes, as reported previously.^{52–54} From the results of XRD (details in Supporting Information), we confirm that the crystallinity of the MAPbI₃ thin film does not significantly change due to the introduction of nanostructures. From the energy-dispersive spectrometer (EDS), we can see that the MAPbI₃ film on the nanopillar substrate shows good element distribution (Element: I, O, Pb, Si, C, and N) (Figure S7).

3.3. Performance of Photodetector Devices. In all subsequent tests and characterizations, we selected three sizes of nanopillar samples, each with at least 5 samples. Tested the following dimensions: S-1 sample, a nanopillar array with a diameter of 1000 nm; S-2 sample, a nanopillar array with a diameter of 500 nm; S-3 sample, a nanopillar array with a diameter of 250 nm; a flat SiO₂/Si substrate. Then, we prepared MAPbI₃ thin films on these substrates (Figure S8 in the Supporting Information) and evaporated copper electrodes to prepare devices for subsequent testing. First, we tested the absorption spectra of MAPbI₃ grown on different substrates (S-1, S-2, S-3, flat substrate) to examine its light absorption ability. From the results, we found that compared to the flat substrate, the absorbance of MAPbI₃ thin films on the substrates with nanopillar structure increased by ~10% (Figure 3a). These results have been reported in previous reports,^{16,51,55–57} indicating that in the visible light range, the introduction of nanopillars' structure can increase the scattering and decrease the reflection of light within the MAPbI₃ film, thus enhancing the light absorption of MAPbI₃ film. From the PL spectrum (Figure S9), the absorption edge around 750 nm is related to the optical absorption of the perovskite as well as the PL peak at around 780 nm. These results are consistent with those found in the scientific literature.⁵⁸

Then, we designed and fabricated a photodetector array to test the photoelectronic characteristics of devices based on nanopillar array substrates. To prevent mutual influence between different devices, the interdigital electrode of our designed photodetector has an aspect ratio of 1/41. (The channel length and width of the photodetector are 50 and 2050 μm, respectively, Figure S10.) Figure 3b shows photodetectors' typical current versus voltage (*I*–*V*) curves based on S-2 and flat substrate measured in the dark and under white light illumination at 2.5 mW/cm². The photodetectors based on S-2 samples showed considerably higher current (*I*_{light} = 1.42 × 10^{−5} A) under white light illumination, which is 2317 times larger (at 5 V bias) than that in the darkness (*I*_{dark} = 6.12 × 10^{−9} A), while the photodetectors with flat substrate just showed 253 times larger (at 5 V bias) current under the same illumination (*I*_{light} = 1.53 × 10^{−6} A) as that in the darkness (*I*_{dark} = 6.04 × 10^{−9} A), which is similar to prior reports.^{59–61} We also measured S-1 and S-3 samples and observed similar photocurrents to S-2 samples (Figure S11). Therefore, we found that the introduction of nanopillar array substrates can

improve the photoelectric performance of MAPbI₃ thin film devices. These photodetectors have good stability, which exhibited stable performance after 72 h of exposure to air (Figure S12).

We further investigated the incident light intensity dependence of photodetectors. Figure 3c depicts the *I*–*V* curves measured by a photodetector based on S-2 under visible light and dark conditions with different light intensities. The light intensity of white light is 5, 50, 0.3, 0.5, and 1 mW/cm², respectively.

In photodetectors, the responsivity (*R*) represents the signal strength under illumination, which can be calculated using

$$R = \frac{J_{\text{ph}} - J_{\text{dark}}}{L_{\text{light}}} \quad (1)$$

Here, *J*_{ph} is the photocurrent density, *J*_{dark} is the dark current density, and *L*_{light} is the incident light intensity.⁶²

From eq 1, the *R* values of the photodetectors based on nanopillar substrates (S-2 samples) are calculated to be 7.1 A/W (under white light at 5 μW/cm²) (Figure 3d). Figure 3e shows the On–Off diagram measured by a photodetector based on the S-2 sample under white light at 2.5 mW/cm²; the *I*_{light} and *I*_{dark} remain stable every 10 s, which represents the device demonstrating good optoelectronic performance stability. And we tested the *I*–*V* curves of the photodetector based on the S-2 sample measured under visible light at different wavelength under 10 μW/cm² and darkness (Figure 3f), and the *R* values at different wavelengths are shown in Figure 3g.

The specific detectivity (*D*^{*}) is often used to represent the ability of a photodetector to detect weak signals, which can be calculated through the following expression

$$D^* = \frac{(A \cdot f)^{0.5}}{(I_n/R)} \approx \frac{R}{(2q \cdot J_{\text{dark}})^{0.5}} \quad (2)$$

Here, *A* is the effective area of the device, *f* is the electrical bandwidth, *I*_n is the noise current, and *q* is the fundamental unit of charge. The *D*^{*} value of the photodetector based on S-2 is 7.3 × 10¹⁰ Jones (at 450 nm). The *D*^{*} values of the photodetector are distributed from 4.1 × 10¹⁰ to 4.6 × 10¹⁰ Jones under a white light intensity range from 5 to 1 mW/cm², which suggests that the device is sensitive to weak light.

The photodetectors based on nanopillar array substrates showed a high sensitivity to visible light, as shown in Figure 3h (under 10 μW/cm² at 380 nm) and Figure 3i (under 10 μW/cm² at 800 nm), which indicates that nanostructures can increase the light absorption in the visible light range.

As Table 1 shows, both *R* and *D*^{*} values of the photodetectors based on nanopillar array structures are at a good level in the photodetectors based on MAPbI₃ films.

To further study the photoresponse enhancement effect of the nanopillar array on MAPbI₃ thin film devices, we made use of optical simulations via COMSOL methods to investigate their optical properties. We simulated the electric field distribution of MAPbI₃ thin films on SiO₂/Si nanopillar substrates and flat substrates, respectively. (The incident light was set at 650 nm and 850 nm on the nanopillars with a height of 400 ± 30 nm and a diameter of 300 nm.) Figure 3k shows the enhancement of the electric field between nanopillar structures and periodic fluctuations along the nanopillar array, as the nanopillar array allows for repeated reflections of

Table 1. Comparison of the Key Parameters of Photodetectors Based on Different Materials

Material	Light source	R (A/W)	D* (Jones)	Refs
MAPbI ₃ nanopillars	White light	7.1	2.9 × 10 ¹⁰	this work
MAPbI ₃ nanopillars	450 nm	11.2	7.3 × 10 ¹⁰	this work
MAPbI ₃ film	White light	0.2		ref 63
	670 nm	0.3		ref 64
	365 nm	3.5		ref 65
MAPbI ₃ network	650 nm	0.1	1.0 × 10 ¹²	ref 66
MAPbI ₃ nanonet	White light	0.6		ref 67
	700 nm	10.3		
MAPbI ₃ nanoflake	265 nm	12.0	1.0 × 10 ¹¹	ref 68
MAPbI ₃ porous photonic crystals	White light	12.7	3.2 × 10 ¹³	ref 69

incident light. On the contrary, the electric field distribution on the flat substrate remains unchanged and is uniform (Figure 3j). Therefore, introducing a nanopillar array structure into the MAPbI₃ film can increase its light absorption and sensitivity, which is consistent with the experimental results.

3.4. Application of Image Sensors. Photodetectors are widely used in the field of image sensors. We have fabricated an image sensor composed of a 5 × 5 photodetector array. The size of each photodetector is 450 μm × 750 μm. As shown in Figure 4a, we used a hollowed out “T”-shaped metal mask (1.5 cm × 1.5 cm) and placed it on photodetectors to manufacture an image sensor. Figure 4b shows that the photoresponse of a single photodetector under white light at a bias voltage of 5.0 V is stable. When the light is turned off, the “T” character cannot

be recognized (Figure 4c) because all photodetectors display low dark current (<4.5 × 10⁻⁸ A). On the contrary, when the light is turned on, the photocurrent of all photodetectors below the character “T” has significantly increased (>2.5 × 10⁻⁶ A), showing good resolution. Although due to incomplete shading, there is a small amount of light transmission, resulting in a slight increase (<3.5 × 10⁻⁷ A) in the current of the photodetector in the obstructed area; it is still much smaller than the photocurrent under direct illumination. Therefore, the character “T” can be recognized through mapping the photocurrent (Figure 4d).

4. CONCLUSIONS

In summary, we have prepared a large-area tunable SiO₂/Si nanopillar array via nanosphere lithography and dry etching and demonstrated its applications in improving the photosensitivity of perovskite materials. The SEM and XRD results indicate that the nanopillar array does not significantly decrease the crystallinity of MAPbI₃ thin films. Experimental results and COMSOL simulation results demonstrate that nanopillar arrays can improve light absorption and enhance the electric field within the nanopillar arrays covered by MAPbI₃ thin films, resulting in higher photosensitivity of MAPbI₃ thin films. The photodetector with nanopillar structures exhibited responsivity with 11.2 A/W and specific detectivity of 7.3 × 10¹⁰ Jones at 450 nm. In comparison to devices based on flat substrates, these photodetectors exhibit better light absorption ability in the visible light range, which is attributed to the light enhancement effect brought about by the nanopillar array structure. Additionally, an image sensor array was fabricated, and it demonstrated high-contrast image sensing. The nanopillar arrays are also suitable for other light-sensing materials such as InGaAs, GaN, CdS, and TiO₂.

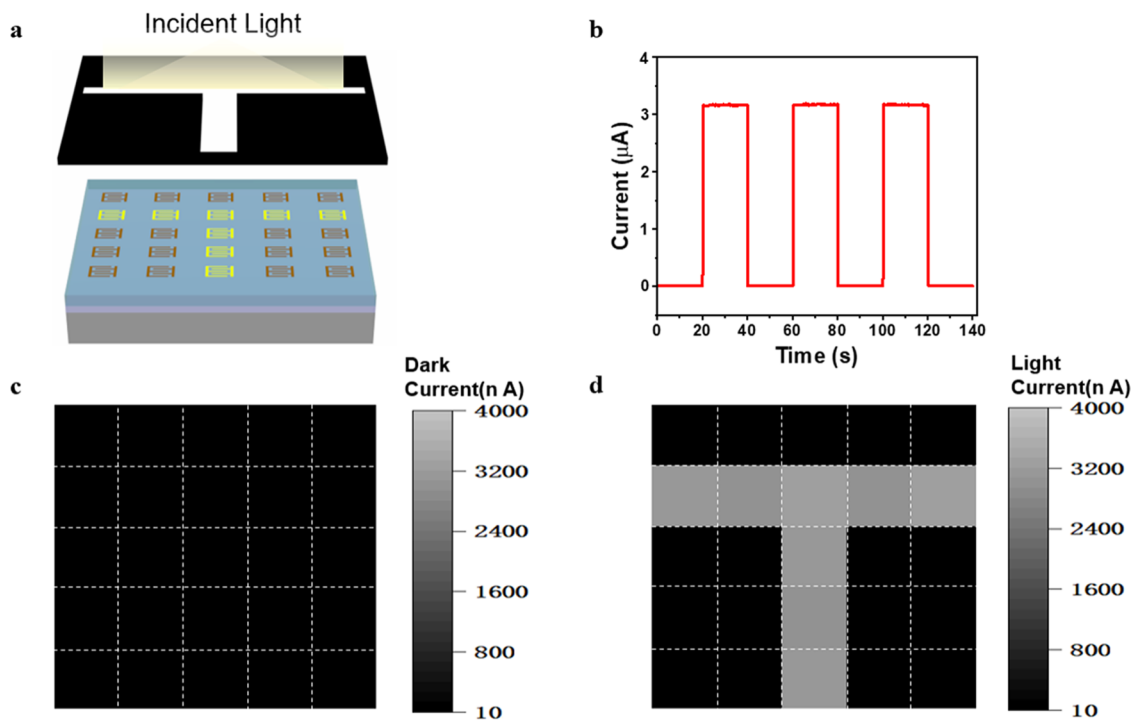


Figure 4. (a) Schematic illustration of a photodetector array with 5 × 5 pixels. (b) Time-resolved photoresponse of the photodetector based on a MAPbI₃ film on a SiO₂/Si nanopillar substrate (S-2 sample) under white light (1 mW/cm²). (c, d) Output results of the photodetector array in darkness and under illumination, respectively.

■ ASSOCIATED CONTENT

SI Supporting Information

The Supporting Information is available free of charge at <https://pubs.acs.org/doi/10.1021/acsomega.3c07390>.

Materials and methods, Figures (S1–S12) include SEM images of periodic nanostructures (PS nanospheres, Si nanopillar arrays, SEM images of the MAPbI₃ film on flat and nanopillar substrates, single photodetector based on a MAPbI₃ film on a SiO₂/Si nanopillar substrate), images of MAPbI₃ thin-film spin-coated on a nanopillar array with different diameters, EDS of MAPbI₃ film based on nanopillars substrate, dark/photocurrent of the photodetectors based on S-1 and S-3 samples, a histogram of the particle size distribution of MAPbI₃ film fabricated on the flat substrate and nanopillar substrate, photoluminescence spectra of the MAPbI₃ film in different substrates, and the *I*–*V* test for S-2 after 72 h, with a light intensity of 1 mW/cm² under white light illumination (PDF)

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Author Contributions

Xiaobin Xu, W. L., Xiuzhen Xu, J. G., and Z.Y. conceived the idea. Xiaobin Xu, Dr. Xiuzhen Xu, and W.L. supervised the experiment. Z.Y. and H.K. performed the nanostructure fabrication and characterization. Y.X. and Xiuzhen Xu assisted in the photoelectric measurements. The data analyses were done through the contributions of all the authors. The manuscript was written through the contributions of all authors.

Notes

The authors declare no competing financial interest.

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